



No.5266

2SJ416
P-Channel Silicon MOSFET
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Absolute Maximum Ratings at Ta = 25°C

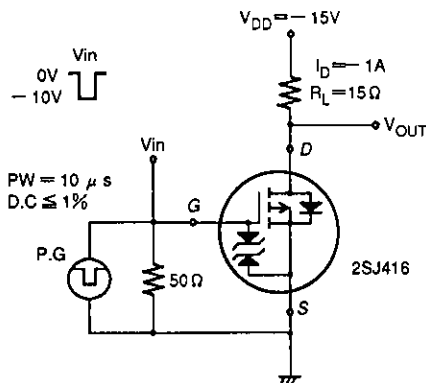
			unit
Drain-to-Source Voltage	V _{DS}	-30	V
Gate-to-Source Voltage	V _{GS}	±20	V
Drain Current(DC)	I _D	-2	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	-8 A
Allowable Power Dissipation	P _D	Mounted on ceramic board (250mm ² × 0.8mm) Tc = 25°C	1.5 W
Channel Temperature	T _{ch}		3.5 W
Storage Temperature	T _{stg}		150 °C
			-55 to +150 °C

Electrical Characteristics at Ta = 25°C

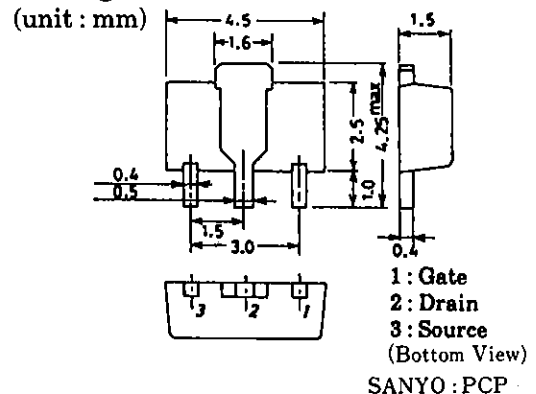
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0			-100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±16V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10V, I _D = -1A	1.2	2.0		S
Static Drain-to-Source ON-State Resistance	R _{DSS(on)}	I _D = -1A, V _{GS} = -10V		310	440	mΩ
ON-State Resistance	R _{DSON}	I _D = -1A, V _{GS} = -4V		480	650	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10V, f = 1MHz		170		pF
Output Capacitance	C _{oss}	V _{DS} = -10V, f = 1MHz		120		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -10V, f = 1MHz		30		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	"		20		ns
Turn-OFF Delay Time	t _{d(off)}	"		110		ns
Fall Time	t _f	"		75		ns
Diode Forward Voltage	V _{SD}	I _S = -2A, V _{GS} = 0	-1.0	-1.2		V

Marking : JJ

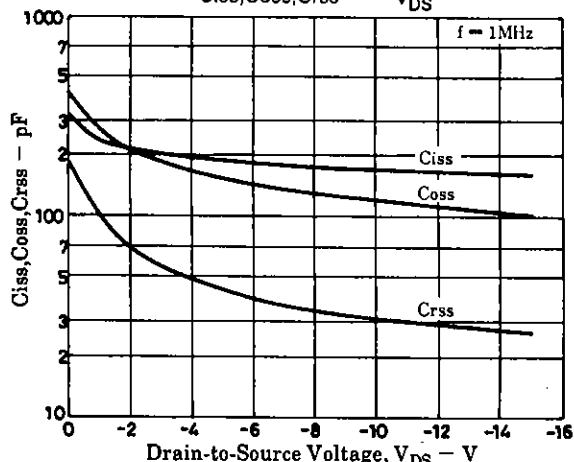
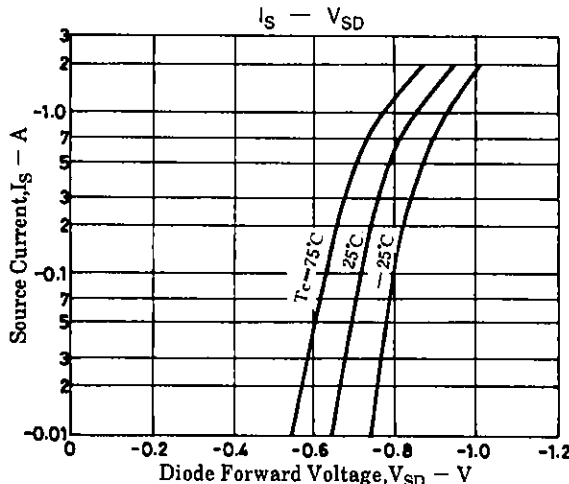
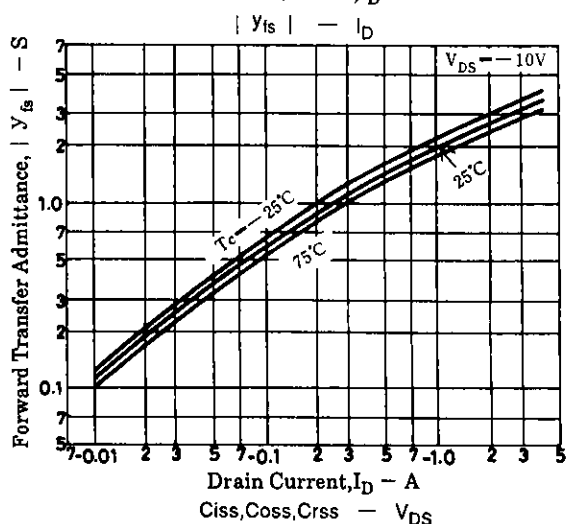
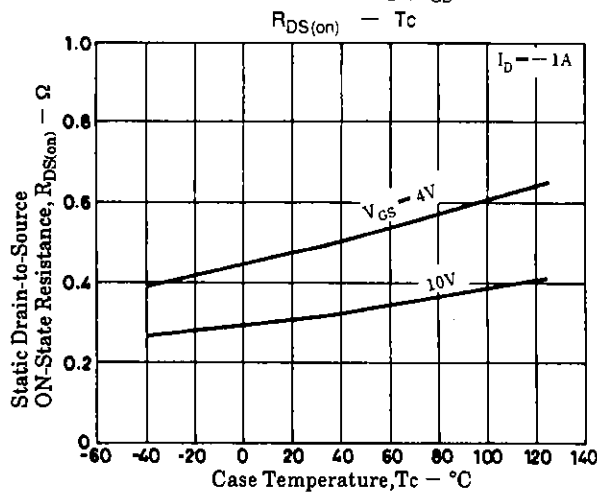
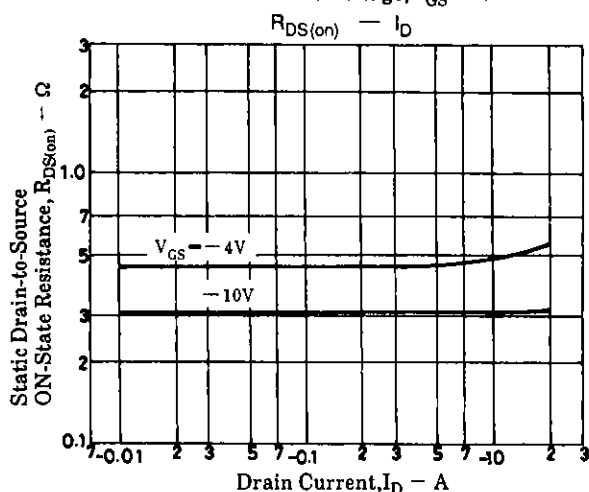
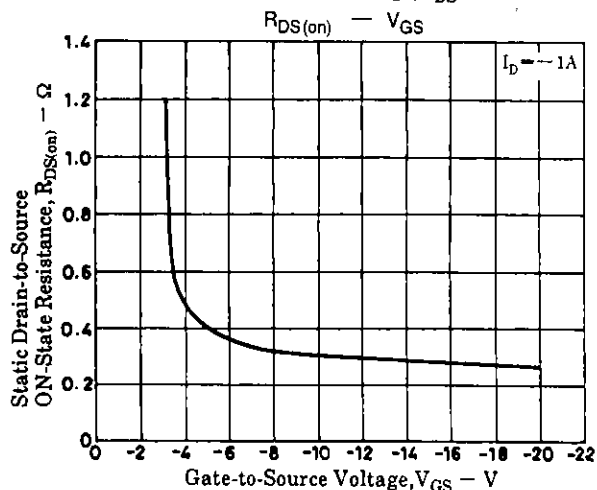
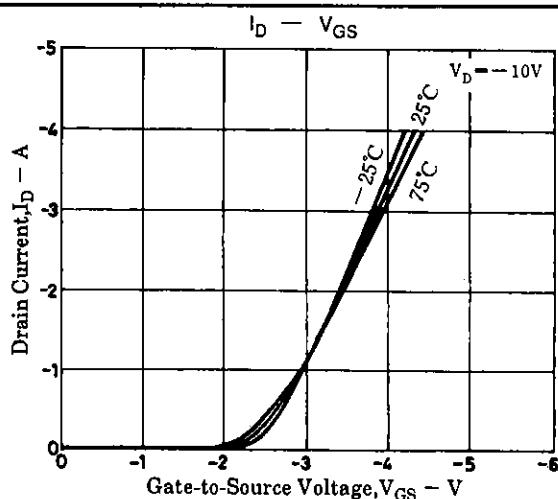
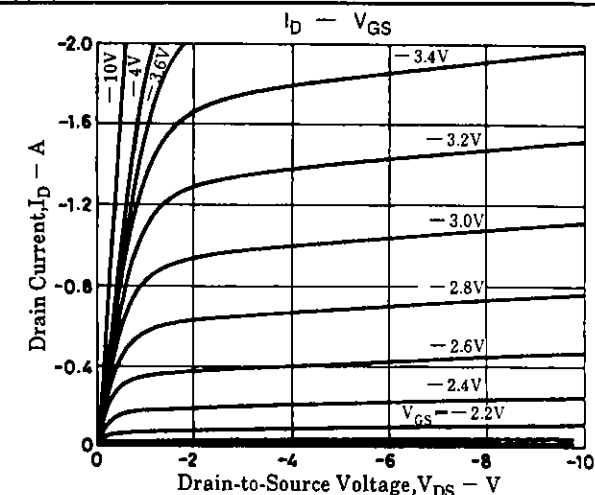
Switching Time Test Circuit

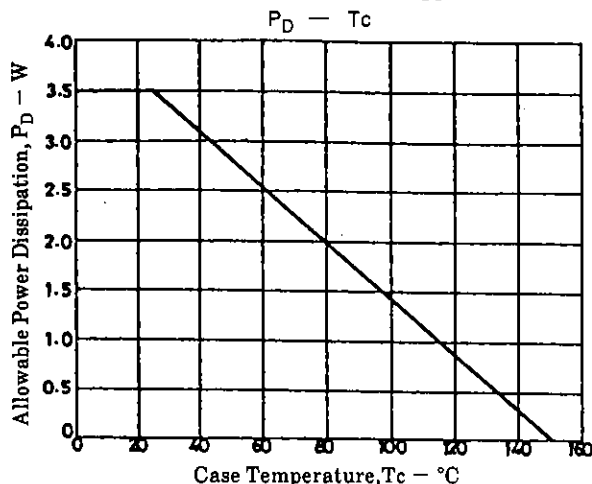
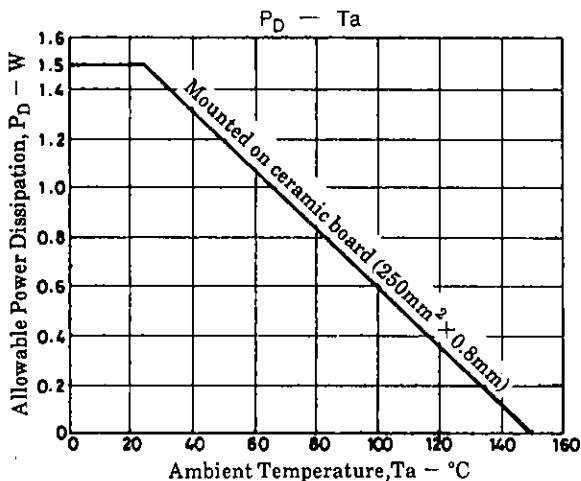
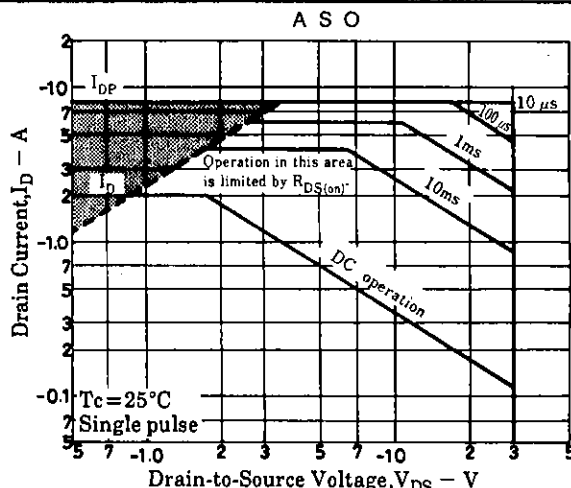
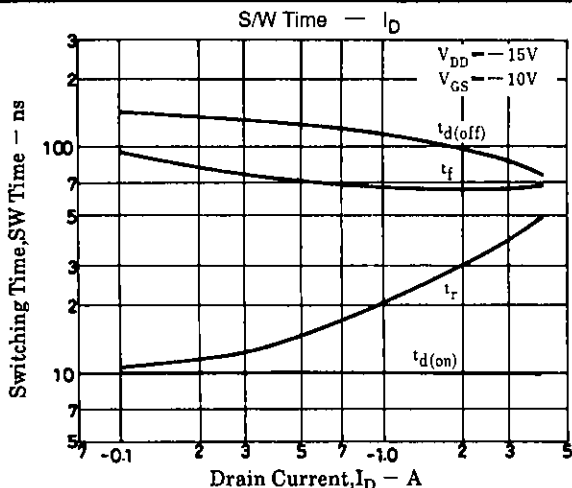


Package Dimensions 2062A



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